



40V N-Channel Enhancement Mode MOSFET

Voltage

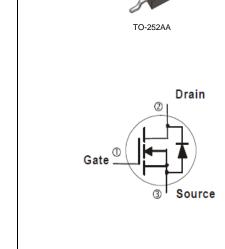
40 V

Current

100 A

Features

- R_{DS(ON)}, V_{GS}@10V, I_D@20A<3.8mΩ
- $R_{DS(ON)}$, $V_{GS}@4.5V$, $I_{D}@10A<5m\Omega$
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard



Mechanical Data

• Case: TO-252AA Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0104 ounces, 0.297grams

$\textbf{Maximum Ratings and Thermal Characteristics} \; (T_A = 25 ^{\circ} \text{C unless otherwise noted})$

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V_{DS}	40	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Continuous Drain Current (Note 4)	T _C =25°C	l _D	100	· · · · · ·	
	T _C =100°C		64	Α	
Pulsed Drain Current (Note 1)	T _C =25°C	I_{DM}	400		
Power Dissipation	T _C =25°C	Po	70	14/	
	T _C =100°C		28	W	
Continuous Drain Current (Note 4)	T _A =25°C	I _D	17	^	
	T _A =70°C		13	А	
Power Dissipation	T _A =25°C	PD	2	W	
	T _A =70°C		1.3		
Single Pulse Avalanche Energy (Note 6)		E _{AS}	312	mJ	
Operating Junction and Storage Temperature Range		T_{J} , T_{STG}	-55~150	°C	
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{ heta JC}$	1.8	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

• Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA V _{DS} =V _{GS} , I _D =250uA	40	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$		1	1.54	2.5		
Drain-Source On-State Resistance	R _{DS(on)}	V_{GS} =10V, I_D =20A	-	2.1	3.8	mΩ	
		V _{GS} =4.5V, I _D =10A	-	2.8	5		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V	-	-	1	uA	
Gate-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	<u>+</u> 100	nA	
Dynamic (Note 7)							
Total Gate Charge	Q_g	V _{DS} =20V, I _D =10A, V _{GS} =4.5V (Note 2,3)	-	50	-	nC	
Gate-Source Charge	Q_gs		-	13	-		
Gate-Drain Charge	Q_{gd}		-	19	-		
Input Capacitance	Ciss	V _{DS} =25V, V _{GS} =0V, f=1MHZ	-	5214	-	pF	
Output Capacitance	Coss		-	492	-		
Reverse Transfer Capacitance	Crss		-	246	-		
Turn-On Delay Time	td _(on)	\/ 00\/ I 4A	-	44	-		
Turn-On Rise Time	t _r	V_{DS} =20V, I_{D} =1A, V_{GS} =10V, R_{G} =6 Ω (Note 2,3)	-	43	-	ns	
Turn-Off Delay Time	td _(off)		-	218	-		
Turn-Off Fall Time	t _f		-	62	-		
Drain-Source Diode							
Maximum Continuous Drain-Source	ı		-	-	100	А	
Diode Forward Current	I _S						
Diode Forward Voltage	V_{SD}	I _S =1A, V _{GS} =0V	-	0.65	1	V	

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH, I_{AS}=79A, V_{DD}=25V, V_{GS}=10V, Starting T_J=25°C.
- 7. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

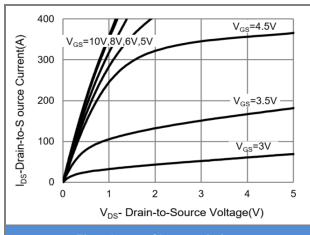


Fig.1 Output Characteristics

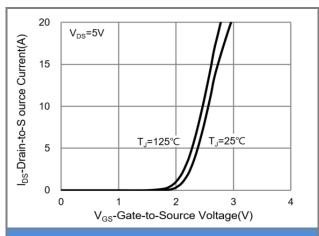


Fig.2 Transfer Characteristics

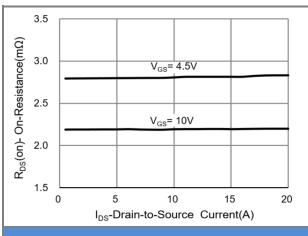


Fig.3 On-Resistance vs. Drain Current

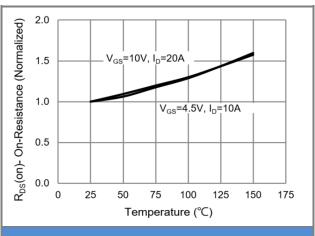


Fig.4 On-Resistance vs. Junction temperature

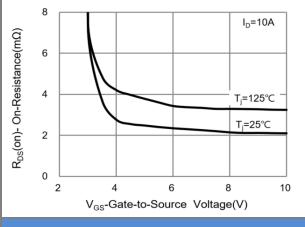


Fig.5 On-Resistance Variation with V_{GS}

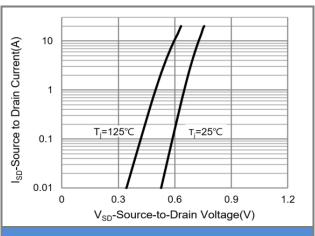


Fig.6 Source-Drain Diode Forward Voltage





TYPICAL CHARACTERISTIC CURVES

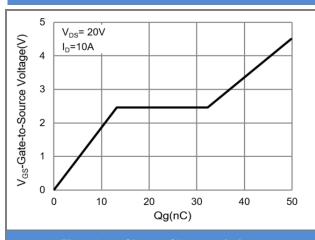


Fig.7 Gate-Charge Characteristics

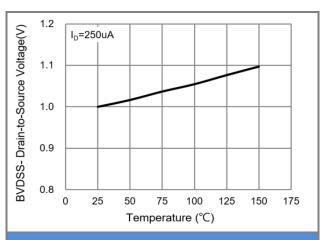


Fig.8 Breakdown Voltage Variation vs. Temperature

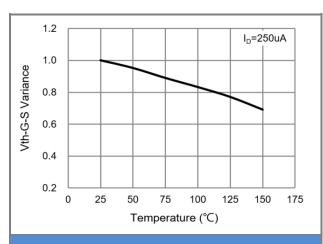


Fig.9 Threshold Voltage Variation with Temperature

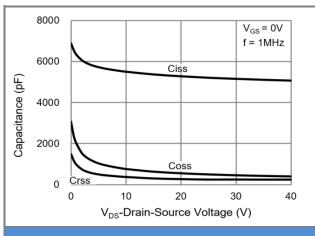
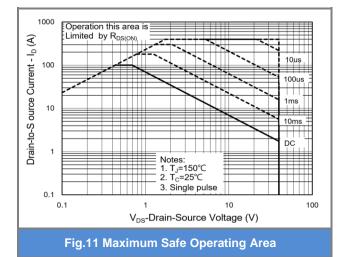


Fig.10 Capacitance vs. Drain-Source Voltage



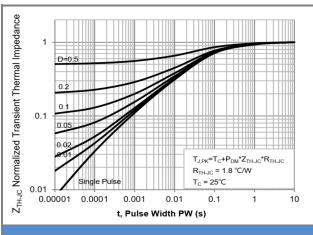


Fig.12 Normalized Transient Thermal Impedance

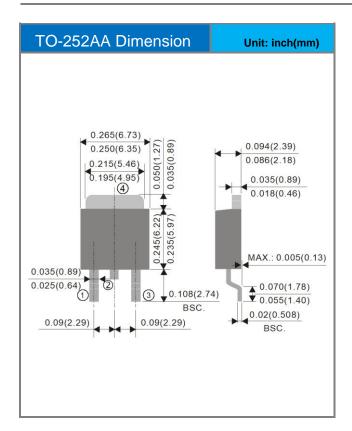


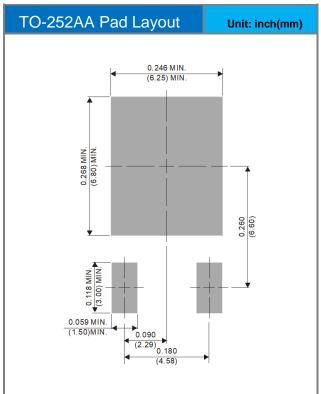


Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJD100N04_L2_00001	TO-252AA	3,000pcs / 13" reel	D100N04	Halogen free

Packaging Information & Mounting Pad Layout









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